

TRANSISTOR MODULE

QCA150AA120

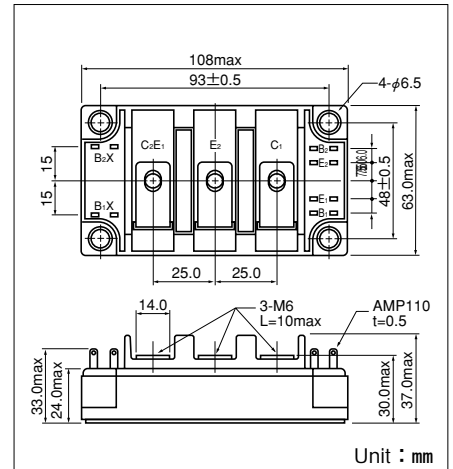
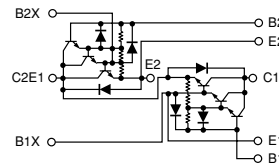
UL:E76102(M)

QCA150AA120 is a dual Darlington power transistor module which has series-connected high speed, high power Darlington transistors. Each transistor has a reverse paralleled fast recovery diode. The mounting base of the module is electrically isolated from semiconductor elements for simple heatsink construction,

- $I_C=150A$, $V_{CEX}=1200V$
- Low saturation voltage for higher efficiency.
- High DC current gain h_{FE}
- Isolated mounting base

(Applications)

Motor Control (VVVF), AC/DC Servo, UPS, Switching Power Supply, Ultrasonic Application



Maximum Ratings

($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Item	Conditions	Ratings		Unit
			QCA150AA120		
V_{CBO}	Collector-Base Voltage		1200		V
V_{CEX}	Collector-Emitter Voltage	$V_{BE}=-2V$	1200		V
V_{EBO}	Emitter-Base Voltage		10		V
I_C	Collector Current		150		A
$-I_C$	Reverse Collector Current		150		A
I_B	Base Current		8		A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	1000		W
T_j	Junction Temperature		-40 to +150		$^\circ\text{C}$
T_{stg}	Storage Temperature		-40 to +125		$^\circ\text{C}$
V_{iso}	Isolation Voltage	A.C.1minute	2500		V
	Mounting Torque	Mounting (M6)	Recommended Value 2.5-3.9 (25-40)	4.7 (48)	N·m
		Terminal (M6)	Recommended Value 2.5-3.9 (25-40)	4.7 (48)	(kgf·cm)
	Mass	Typical Value	470		g

Electrical Characteristics

Symbol	Item	Conditions	Ratings		Unit
			Min.	Max.	
I_{CBO}	Collector Cut-off Current	$V_{CB}=1200V$		2.0	mA
I_{EBO}	Emitter Cut-off Current	$V_{EB}=10V$		600	mA
$V_{CEX(SUS)}$	Collector Emitter Sustaining Voltage	$I_C=30A$, $I_{B2}=-6A$	1200		V
h_{FE}	DC Current Gain	$I_C=150A$, $V_{CE}=5V$	75		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=150A$, $I_B=3A$		3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=150A$, $I_B=3A$		3.5	V
t_{on}	Switching Time	On Time		3.0	μs
t_s		Storage Time	$V_{CC}=600V$, $I_C=150A$ $I_{B1}=3A$, $I_{B2}=-3A$	15.0	
t_f		Fall Time		3.0	
V_{ECO}	Collector-Emitter Reverse Voltage	$-I_C=150A$		1.8	V
$R_{th(j-c)}$	Thermal Impedance (junction to case)	Transistor part		0.125	$^\circ\text{C/W}$
		Diode part		0.6	